

MARKED AMENDED CLAIMS

SERIAL NO. 09/612,551

DOCKET NO. NEC WNZ-2212

**MARKED CLAIMS SHOWING CHANGES MADE**

1. (Twice Amended) A semiconductor thin film forming [system for] method comprising:

modifying a predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a projected light patterned through plural patterns formed on a photo mask[,]; and

[said system comprising a mechanism for] uniformizing the light to be applied in such a manner that the intensity of said light in a predetermined area on the photo mask distributes within a range of  $\pm 11.2\%$  of the average intensity of said light in said area[;],

wherein spatial distribution of peak intensity of light projected and applied on the semiconductor thin film is uniformized to an identical extent with the peak intensity of the intensity distribution on the photo mask.

17. (Amended) [A system] The method according to claim 1, wherein said projected light comprises a laser [source] beam.

18. (Amended) [A system] The method according to claim 17, wherein said laser [source comprises] beam is generated by an excimer laser.

19. (Amended) [A system] The method according to claim 17, wherein said [mechanism for uniformizing] light is uniformized using [the light comprises] a homogenizer, a mask and a projection lens through which said light is applied.

20. (Amended) [A system] The method according to claim 19, wherein said mask includes a slit for throttling light passed through the homogenizer into a rectangular beam.

21. (Amended) A [system] method according to claim 19, [and further including] wherein a projection lens is used for reducing and projecting a slit image of the mask onto said film.

22. (Amended) A semiconductor thin film forming [system for] method comprising:  
modifying a predetermined region of a semiconductor thin film by exposing the  
semiconductor thin film to a projected light patterned through plural patterns formed on a photo  
mask,  
wherein said light is applied in such a manner that the intensity of said light in a  
predetermined area on the photo mask is distributed within a range of  $\pm 11.2\%$  of an average  
intensity of said light in said area.